

IN THE ABSTRACT

Please rewrite the abstract as shown below.

ONE TIME PROGRAMMING MULTIPLE LEVEL MEMORY CELLS

ABSTRACT

A multiple-level memory cell comprising: ~~a memorization~~ including a storage element formed of several polysilicon resistors ~~associated~~ connected in series between two input/output terminals; and a load in series with said resistive element, the midpoint of this series ~~association~~ connection forming a read terminal of the memory cell, and the respective junction points of said resistors of the ~~memorization~~ storage element being accessible.